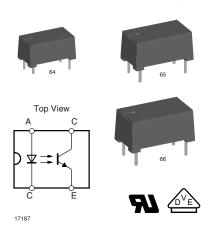
### Vishay Semiconductors



# Optocoupler, Phototransistor Output, Very High Isolation Voltage



### **DESCRIPTION**

The CNY64/CNY65/CNY66 consist of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4 pin plastic package.

The single components are mounted opposite one another, providing a distance between input and output for highest safety requirements of > 3 mm.

#### **VDE STANDARDS**

These couplers perform safety functions according to the following equipment standards:

- DIN EN 60747-5-5 (VDE 0884)
   Optocoupler for electrical safety requirements
- IEC 60950/EN 60950
- Office machines (applied for reinforced isolation for mains voltage ≤ 400 V<sub>RMS</sub>)
- VDE 0804
  - Telecommunication apparatus and data processing
- IEC 60065
  - Safety for mains-operated electronic and related household apparatus
- VDE 0700/IEC 60335
  - Household equipment
- VDE 0160
  - Electronic equipment for electrical power installation
- VDE 0750/IEC 60601 Medical equipment

### **FEATURES**

- Rated recurring peak voltage (repetitive)  $V_{IORM} = 1000 \ V_{RMS}$
- Thickness through insulation ≥ 3 mm
- Creepage current resistance according to VDE 0303/IEC 60112 comparative tracking index: CTI ≥ 200



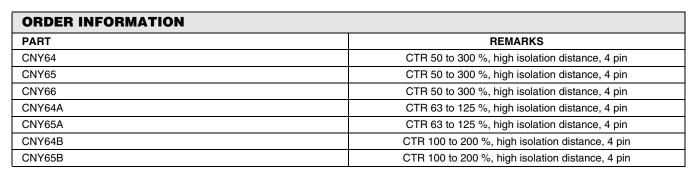
- · Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

### **APPLICATIONS**

- Switch-mode power supplies
- · Line receiver
- · Computer peripheral interface
- · Microprocessor system interface
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
  - for appl. class I IV at mains voltage ≤ 300 V
- for appl. class I IV at mains voltage ≤ 600 V
- for appl. class I III at mains voltage ≤ 1000 V according to DIN EN 60747-5-5 (VDE 0884)

### **AGENCY APPROVALS**

- UL1577, file no. E76222 system code H, J, and K, double protection
- DIN EN 60747-5-5 (VDE 0884)
- VDE related features:
  - rated impulse voltage (transient overvoltage),  $V_{\text{IOTM}} = 8 \text{ kV}$  peak
- isolation test voltage (partial discharge test voltage),  $V_{pd} = 2.8 \text{ kV}$  peak





## Optocoupler, Phototransistor Output, Vishay Semiconductors Very High Isolation Voltage

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
INPUT							
Reverse voltage		V <sub>R</sub>	5	V			
Forward current		I <sub>F</sub>	75	mA			
Forward surge current	t <sub>P</sub> ≤ 10 μs	I <sub>FSM</sub>	1.5	Α			
Power dissipation		P <sub>diss</sub>	120	mW			
Junction temperature		Tj	100	°C			
OUTPUT							
Collector emitter voltage		V <sub>CEO</sub>	32	V			
Emitter collector voltage		V <sub>ECO</sub>	7	V			
Collector current		I <sub>C</sub>	50	mA			
Collector peak current	$t_P/T = 0.5, t_P \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA			
Power dissipation		P <sub>diss</sub>	130	mW			
Junction temperature		Tj	100	°C			
COUPLER							
AC Isolation test voltage (RMS)	t = 1 min	V <sub>ISO</sub>	8.2	kV			
Total power dissipation		P <sub>tot</sub>	250	mW			
Ambient temperature range		T <sub>amb</sub>	- 55 to + 85	°C			
Storage temperature range		T <sub>stg</sub>	- 55 to + 100	°C			
Soldering temperature	2 mm from case, ≤ 10 s	T <sub>sld</sub>	260	°C			

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTICS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	I <sub>F</sub> = 50 mA	V <sub>F</sub>		1.25	1.6	V		
Junction capacitance	V <sub>R</sub> = 0, f = 1 MHz	Cj		50		pF		
OUTPUT								
Collector emitter voltage	I <sub>C</sub> = 1 mA	$V_{CEO}$	32			V		
Emitter collector voltage	I <sub>E</sub> = 100 μA	V <sub>ECO</sub>	7			V		
Collector emitter leakage current	V <sub>CE</sub> = 20 V, I <sub>f</sub> = 0 A	I <sub>CEO</sub>			200	nA		
COUPLER								
Collector emitter saturation voltage	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 1 mA	V <sub>CEsat</sub>			0.3	V		
Cut-off frequency	$V_{CE}$ = 5 V, $I_F$ = 10 mA, $R_L$ = 100 $\Omega$	f <sub>c</sub>		110		kHz		
Coupling capacitance	f = 1 MHz	C <sub>k</sub>		0.3		pF		

#### Note

 $T_{amb} = 25$  °C, unless otherwise specified. Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I <sub>C</sub> /I <sub>F</sub>			CTR	50		300	%
		CNY64A	CTR	63		125	%
	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	CNY65A	CTR	63		125	%
	<u> </u>	CNY64B	CTR	100		200	%
		CNY65B	CTR	100		200	%

### Vishay Semiconductors Optocoupler, Phototransistor Output, Very High Isolation Voltage



MAXIMUM SAFETY RATINGS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT	INPUT							
Forward current		I <sub>F</sub>			120	mA		
OUTPUT								
Power dissipation		P <sub>diss</sub>			250	mW		
COUPLER								
Rated impulse voltage		V <sub>IOTM</sub>			10	kV		
Safety temperature		T <sub>si</sub>			150	°C		

#### Note

According to DIN EN 60747-5-5 (see figure 1). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Partial discharge test voltage - routine test	100 %, t <sub>test</sub> = 1 s	$V_{pd}$	2.8			kV	
Partial discharge test voltage - lot test (sample test)	t <sub>Tr</sub> = 60 s, t <sub>test</sub> = 10 s, (see figure 2)	$V_{pd}$	2.2			kV	
Insulation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C	R <sub>IO</sub>	10 <sup>12</sup>			Ω	
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	10 <sup>11</sup>			Ω	
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 150 °C (construction test only)	R <sub>IO</sub>	10 <sup>9</sup>			Ω	

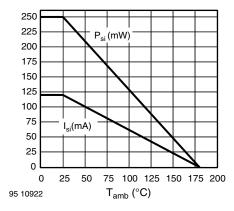


Fig. 1 - Derating Diagram

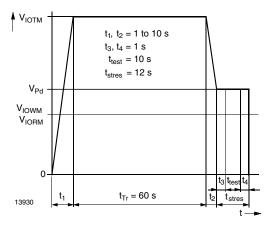


Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5/DIN EN 60747-; IEC 60747

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see figure 3)}$	t <sub>d</sub>		2.6		μs	
Rise time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$ , (see figure 3)	t <sub>r</sub>		2.4		μs	
Fall time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$ , (see figure 3)	t <sub>f</sub>		2.7		μs	
Storage time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$ , (see figure 3)	t <sub>s</sub>		0.3		μs	
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$ , (see figure 3)	t <sub>on</sub>		5.0		μs	
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$ , (see figure 3)	t <sub>off</sub>		3.0		μs	
Turn-on time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega$ , (see figure 4)	t <sub>on</sub>		25.0		μs	
Turn-off time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega, \text{ (see figure 4)}$	t <sub>off</sub>		42.5		μs	



## Optocoupler, Phototransistor Output, Vishay Semiconductors Very High Isolation Voltage

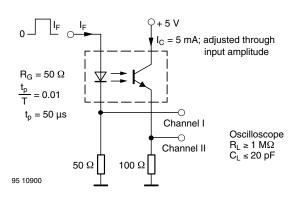


Fig. 3 - Test Circuit, Non-Saturated Operation

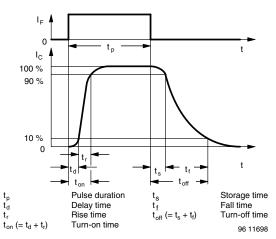


Fig. 5 - Switching Times

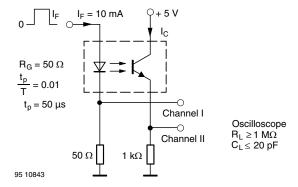


Fig. 4 - Test Circuit, Saturated Operation

### **TYPICAL CHARACTERISTICS**

T<sub>amb</sub> = 25 °C, unless otherwise specified

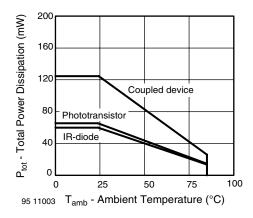


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

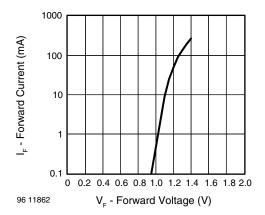


Fig. 7 - Forward Current vs. Forward Voltage

### Vishay Semiconductors

### Optocoupler, Phototransistor Output, Very High Isolation Voltage

100



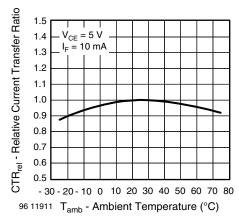
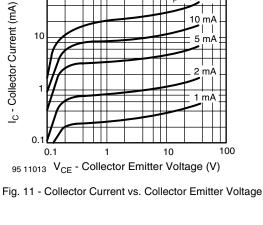


Fig. 8 - Relative Current Transfer Ratio vs. **Ambient Temperature** 



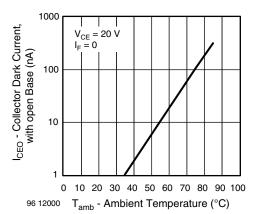


Fig. 9 - Collector Dark Current vs. Ambient Temperature

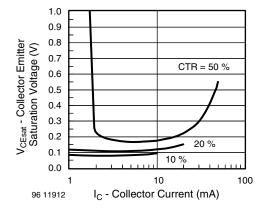


Fig. 12 - Collector Emitter Saturation Voltage vs. Collector Current

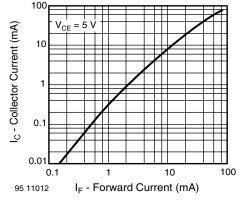


Fig. 10 - Collector Current vs. Forward Current

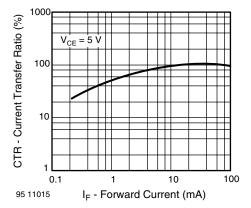


Fig. 13 - Current Transfer Ratio vs. Forward Current



## Optocoupler, Phototransistor Output, Vishay Semiconductors Very High Isolation Voltage

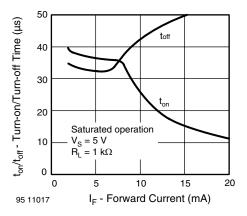


Fig. 14 - Turn-on/Turn-off Time vs. Collector Current

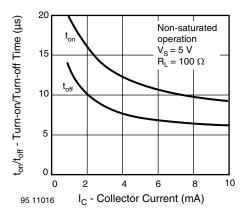
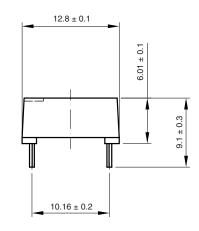
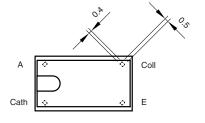


Fig. 15 - Turn-on/Turn-off Time vs. Forward Current

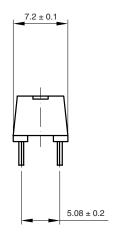
### **PACKAGE DIMENSIONS** in millimeters FOR CNY64



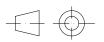


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14765



Weight: ca. 0.73 g Creepage distance: > 9.5 mm Air path: > 9.5 mm after mounting on PC board

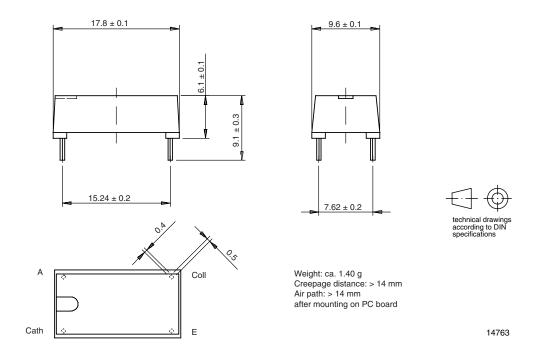


technical drawings according to DIN specifications

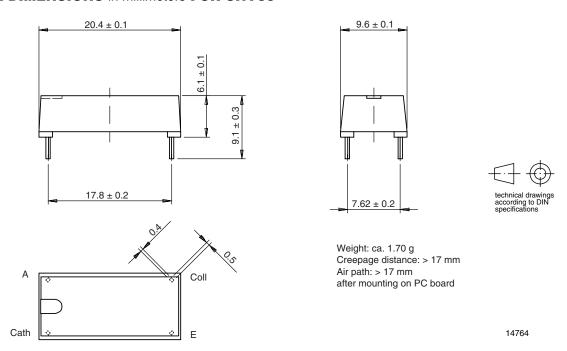
Vishay Semiconductors Optocoupler, Phototransistor Output, Very High Isolation Voltage



### **PACKAGE DIMENSIONS** in millimeters **FOR CNY65**



### **PACKAGE DIMENSIONS** in millimeters FOR CNY66





## Optocoupler, Phototransistor Output, Vishay Semiconductors Very High Isolation Voltage

### **OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

Document Number: 83540 Rev. 1.7, 20-Oct-08



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